SEMICONDUCTOR DEVICE

ABSTRACT

According to the present invention, a semiconductor having excellent yield is provided. The semiconductor device (10) of the present invention includes :
a base material(die pad) (2), a semiconductor element(3), andan adhesive layer(1) intervening the space between the base material and the semiconductor element (3) to adhere the base material and the semiconductor element. Thermal conductive filler (8) is contained in the adhesive layer (1), andwhen the content of the thermal conductive filler dispersed in the whole of the adhesive layer is expressed as C,
the content of the thermal conductive filler in the region 1 ranging from the interface of the adhesive layer at the side of the semiconductor element to the depth by 2μm is expressed as C1, and the content of the thermal conductive filler in the region 2 ranging from the interface of the adhesive layer at the side of the base material to the depth by 2μm is expressed as C2, the following formulae are satisfied:
C1<C, and C2<C.

Fig. 1